

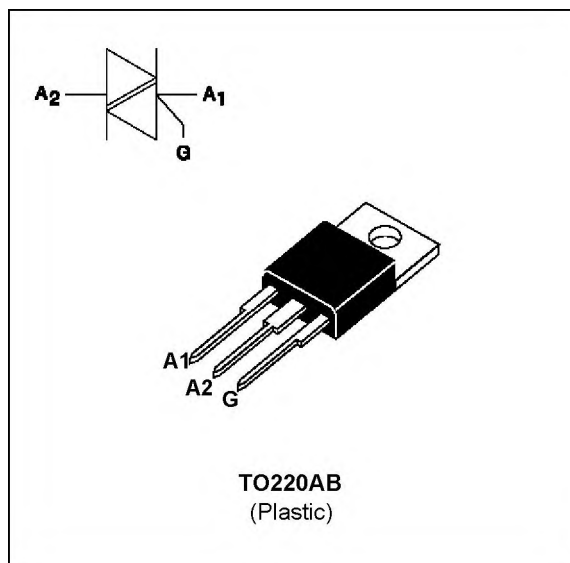
STANDARD TRIACS

FEATURES

- HIGH SURGE CURRENT CAPABILITY
- COMMUTATION : $(dV/dt)_c > 5 \text{ V}/\mu\text{s}$
- BTA Family :
INSULATING VOLTAGE = $2500V_{(RMS)}$
(UL RECOGNIZED : E81734)

DESCRIPTION

The BTA/BTB12 B/C triac family are high performance glass passivated PNP devices. These parts are suitable for general purpose applications where high surge current capability is required. Application such as phase control and static switching on inductive or resistive load.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter			Value	Unit
I _{T(RMS)}	RMS on-state current (360° conduction angle)	BTA	T _c = 90 °C	12	A
		BTB	T _c = 95 °C		
I _{TSM}	Non repetitive surge peak on-state current (T _j initial = 25°C)		tp = 8.3 ms	125	A
			tp = 10 ms	120	
I ² t	I ² t value		tp = 10 ms	72	A ² s
di/dt	Critical rate of rise of on-state current Gate supply : I _G = 500mA di _G /dt = 1A/μs		Repetitive F = 50 Hz	10	A/μs
			Non Repetitive	50	
T _{stg} T _j	Storage and operating junction temperature range			- 40 to + 150 - 40 to + 125	°C °C
T _l	Maximum lead temperature for soldering during 10 s at 4.5 mm from case			260	°C

Symbol	Parameter	BTA / BTB12-... B/C				Unit
		400	600	700	800	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage $T_j = 125^\circ\text{C}$	400	600	700	800	V

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
Rth (j-a)	Junction to ambient		60	°C/W
Rth (j-c) DC	Junction to case for DC	BTA	3.3	°C/W
		BTB	2.7	
Rth (j-c) AC	Junction to case for 360° conduction angle (F= 50 Hz)	BTA	2.5	°C/W
		BTB	2.0	

GATE CHARACTERISTICS (maximum values)

P_G (AV) = 1W P_{GM} = 10W (tp = 20 μs) I_{GM} = 4A (tp = 20 μs) V_{GM} = 16V (tp = 20 μs).

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions		Quadrant		Suffix		Unit
					B	C	
I _{GT}	V _D =12V (DC) R _L =33Ω	T _j =25°C	I-II-III	MAX	50	25	mA
			IV	MAX	100	50	
V _{GT}	V _D =12V (DC) R _L =33Ω	T _j =25°C	I-II-III-IV	MAX	1.5		V
V _{GD}	V _D =V _{DRM} R _L =3.3kΩ	T _j =110°C	I-II-III-IV	MIN	0.2		V
tgt	V _D =V _{DRM} I _G = 500mA dI _G /dt = 3A/μs	T _j =25°C	I-II-III-IV	TYP	2		μs
I _L	I _G =1.2 I _{GT}	T _j =25°C	I-III-IV	TYP	40	20	mA
			II		70	35	
I _H *	I _T = 500mA gate open	T _j =25°C		MAX	50	25	mA
V _{TM} *	I _{TM} = 17A tp= 380μs	T _j =25°C		MAX	1.5		V
I _{DRM} I _{RRM}	V _{DRM} Rated V _{RRM} Rated	T _j =25°C		MAX	0.01		mA
		T _j =110°C		MAX	0.5		
dV/dt *	Linear slope up to V _D =67%V _{DRM} gate open	T _j =110°C		MIN	250	100	V/μs
(dV/dt) _c *	(dI/dt) _c = 5.3A/ms	T _j =110°C		MIN	10	5	V/μs

* For either polarity of electrode A2 voltage with reference to electrode A1.

ORDERING INFORMATION

Package	IT(RMS)	VDRM / VRRM	Sensitivity Specification	
	A	V	B	C
BTA (Insulated)	12	400	X	X
		600	X	X
		700	X	X
		800	X	X
BTB (Uninsulated)		400	X	X
		600	X	X
		700	X	X
		800	X	X

Fig.1 : Maximum RMS power dissipation versus RMS on-state current ($F=50\text{Hz}$).
(Curves are cut off by $(di/dt)_c$ limitation)

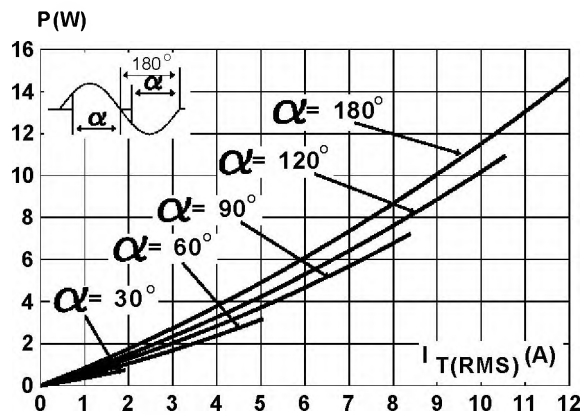


Fig.3 : Correlation between maximum RMS power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact (BTB).

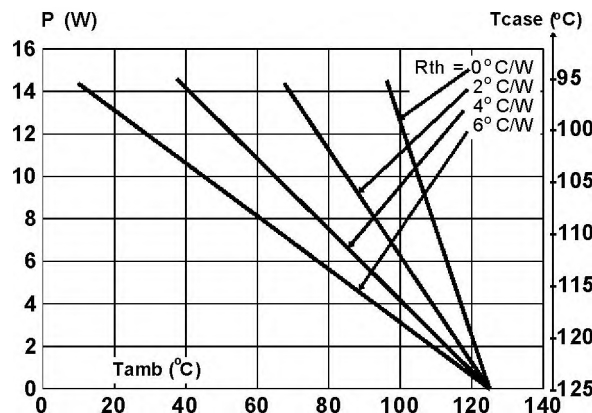


Fig.2 : Correlation between maximum RMS power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact (BTA).

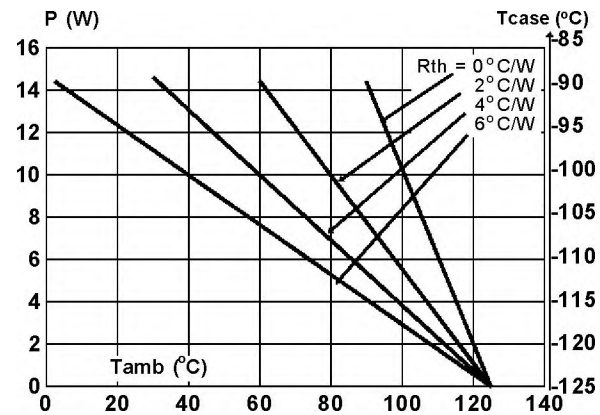


Fig.4 : RMS on-state current versus case temperature.

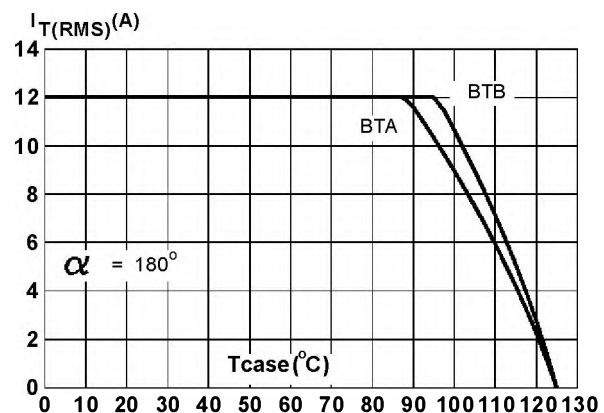


Fig.5 : Relative variation of thermal impedance versus pulse duration.

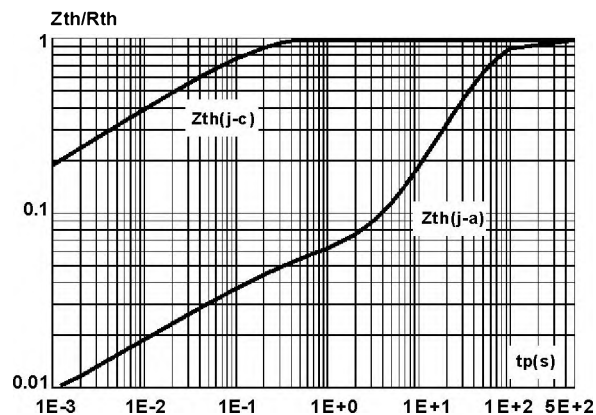


Fig.6 : Relative variation of gate trigger current and holding current versus junction temperature.

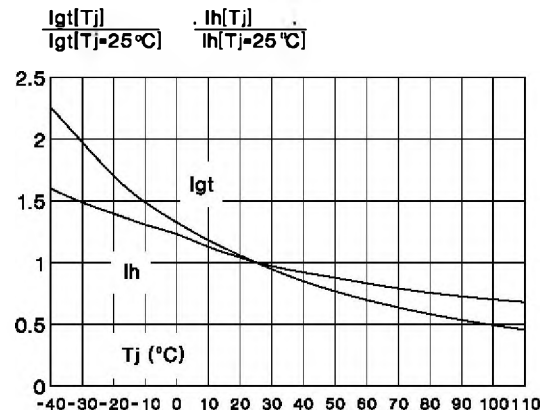


Fig.7 : Non Repetitive surge peak on-state current versus number of cycles.

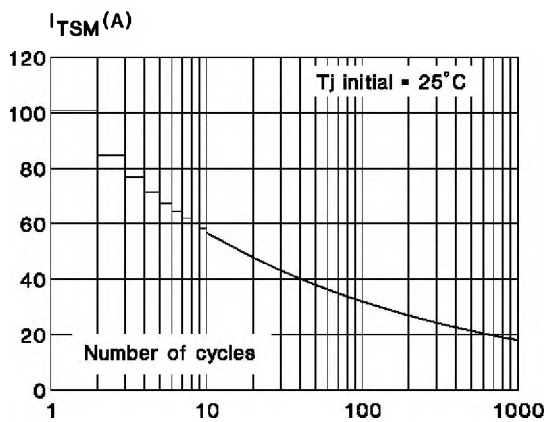


Fig.8 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t \leq 10ms$, and corresponding value of I^2t .

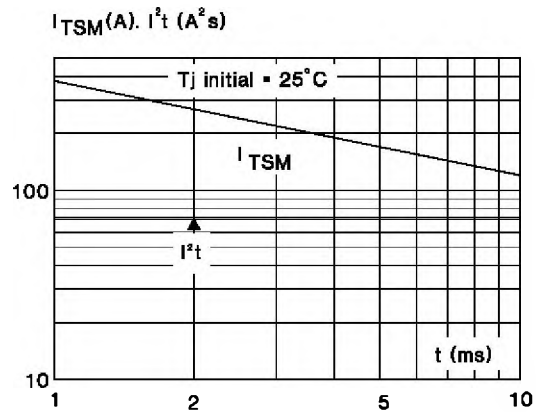
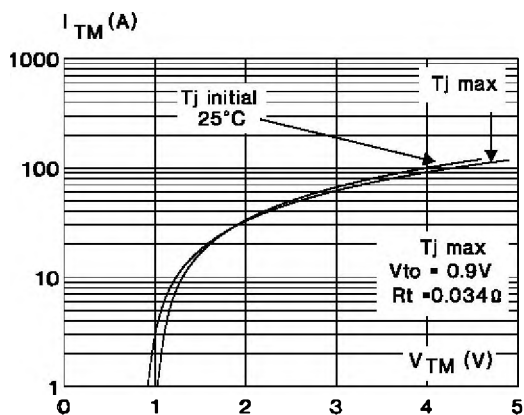
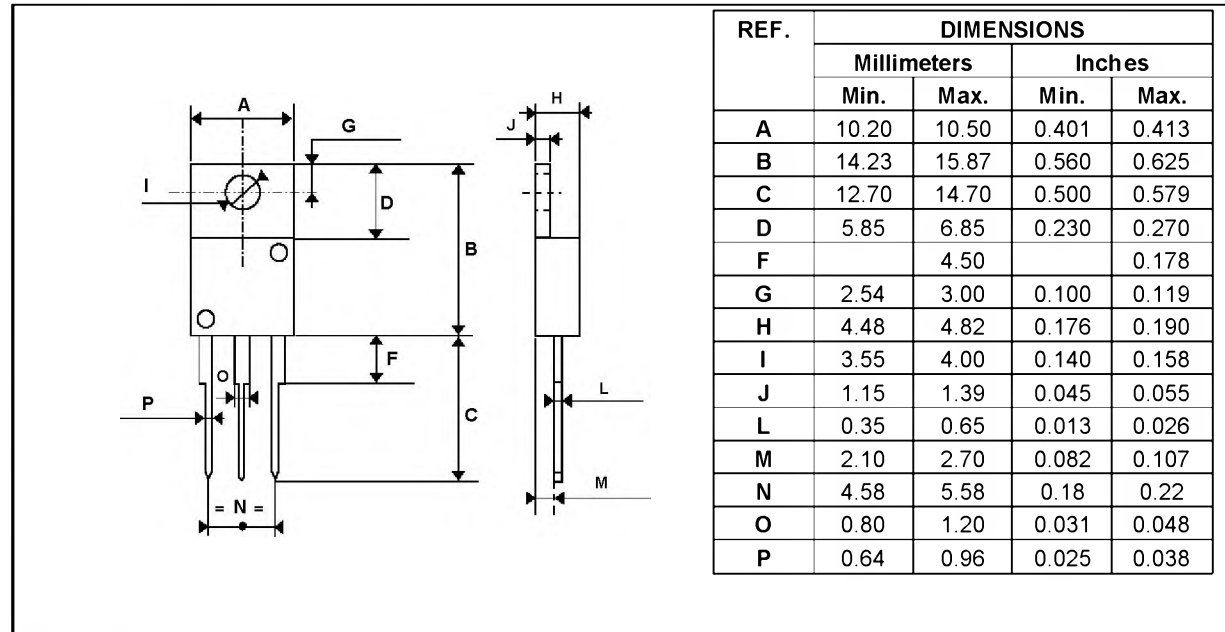


Fig.9 : On-state characteristics (maximum values).



PACKAGE MECHANICAL DATA

TO220AB Plastic



Cooling method : C

Marking : type number

Weight : 2.3 g

Recommended torque value : 0.8 m.N.

Maximum torque value : 1 m.N.

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